

**isc Silicon NPN Power Transistor**

**3DD8F**

**DESCRIPTION**

- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 200V(\text{Min})$
- Collector-Emitter Saturation Voltage-  
:  $V_{CE(sat)} = 2V(\text{Max}) @ I_C = 5A$

**APPLICATIONS**

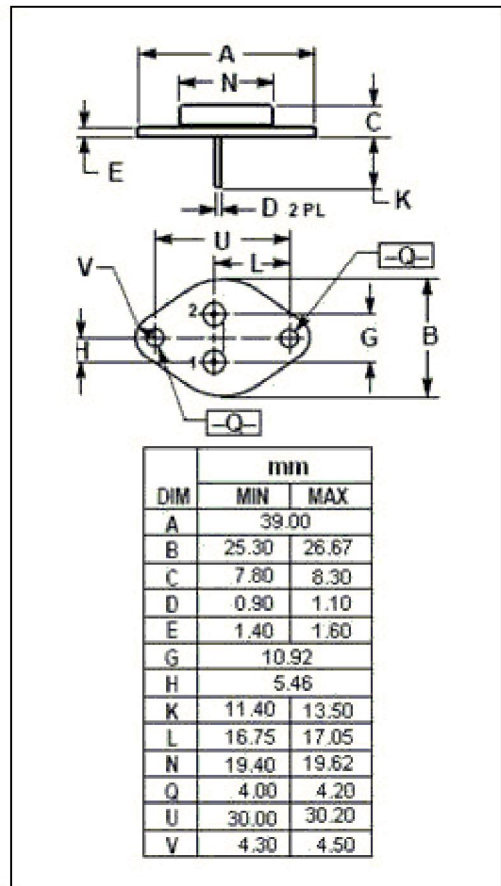
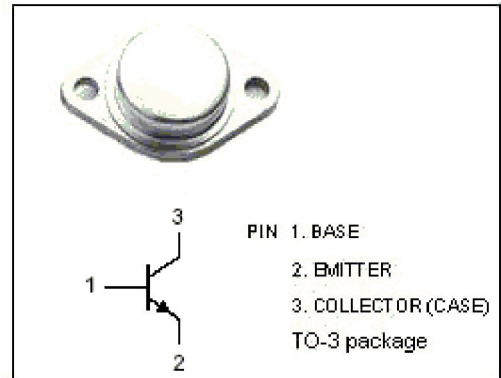
- Designed for power amplifier, low speed switching and regulated power supply applications.

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	200	V
$V_{CEO}$	Collector-Emitter Voltage	200	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	15	A
$P_C$	Collector Power Dissipation @ $T_C=75^\circ\text{C}$	100	W
$T_J$	Junction Temperature	175	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~175	$^\circ\text{C}$

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.0	$^\circ\text{C/W}$



**isc Silicon NPN Power Transistor****3DD8F****ELECTRICAL CHARACTERISTICS****T<sub>c</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 5mA; I <sub>B</sub> = 0	200			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 5mA; I <sub>C</sub> = 0	5			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 5mA; I <sub>E</sub> = 0	200			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 0.5A			2.0	V
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 20V; I <sub>B</sub> = 0			2.0	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 5A; V <sub>CE</sub> = 5V	10			